

MMIC Buffer Amplifier

Mimix Broadband announces a gallium arsenide (GaAs) monolithic microwave integrated circuit (MMIC) three stage buffer amplifier, which can be operated with all three stages biased in parallel, or with independent bias for input and output stages as required to optimize performance. Using 0.15 micron gate length GaAs pseudomorphic high electron mobility transistor (pHEMT) device model technology, this buffer amplifier covers the 16 to 30 GHz frequency band and can be biased for low noise or high power performance. The MMIC device has a small signal gain of 21 dB with a noise figure of 2 dB across the band when biased for low noise. This device also has 18 dBm P1dB compression point at high power bias. This high dynamic range amplifier, identified as XB1004 is suited for wireless communications applications such as millimeter-wave point-to-point radio, local multipoint distribution services (LMDS), SATCOM and VSAT applications.

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